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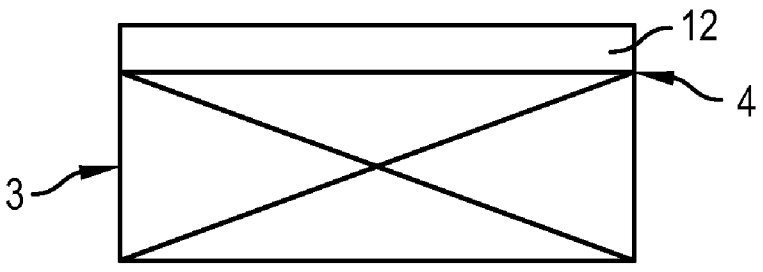
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(54) **Title**: A METHOD FOR MANUFACTURING A HETEROSTRUCTURE AIMING AT REDUCING THE TENSILE STRESS CONDITION OF THE DONOR SUBSTRATE

FIG. 3



(57) **Abstract**: The invention relates to a method for manufacturing a heterostructure, notably intended for applications in the fields of electronics, photovoltaics, optics or optoelectronics, which comprises the following steps: - implantation of atomic species inside a first so-called "donor" substrate (1), so as to form an embrittlement area (11) therein, - assembly of a second so-called "receiver" substrate (3), on the donor substrate (1), - detachment of the rear portion of said donor substrate (1) along the embrittlement area (11) so as to individualize a thin layer of interest (12) on the receiver substrate, wherein said receiver substrate (3) has a larger thermal expansion coefficient than that of the donor substrate (1), and which applies so-called "detachment" annealing after said assembly and before said detachment, in order to facilitate the latter, characterized by the fact that said detachment annealing comprises simultaneous application: - of a first temperature to the donor substrate (1); - of a second temperature, different from the first, to the receiver substrate (3); these first and second temperatures being selected so as to reduce the tensile stress condition of the donor substrate (1).

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